

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	metal adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 07:55
L2	0	metallic adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 07:56
L3	0	metallurgy near (reset adj lines)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 07:56
L4	0	conductive adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 07:56
L5	0	al adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 07:57
L6	0	aluminum adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 08:00
L7	0	ti adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 08:01
L8	0	titanium adj reset adj lines	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 08:02

L9	34	resistance adj random adj access adj memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 08:03
L10	193	resistive adj random adj access adj memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 08:02
L11	12	(resistance adj random adj access adj memory) and (word adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:18
L12	4	(resistance adj random adj access adj memory) and (reset adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:17
L13	3	(resistance adj random adj access adj memory) and (memory adj unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:17
L14	75	(resistive adj random adj access adj memory) and (word adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:24
L15	0	(resistive adj random adj access adj memory) and (reset adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:18
L16	16	(resistive adj random adj access adj memory) and (memory adj unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:34

L17	0	substrate and (word adj line) and (resit adj line) and (dielectric adj (layer or film)) and (memory adj unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:26
L18	0	substrate and (word adj line) and (resit adj line) and (dielectric adj (layer or film)) and (unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:26
L19	0	substrate and (word adj line) and (resit adj line) and (dielectric adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:27
L20	2	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film)) and (memory adj unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:37
L21	1	substrate and (plurality adj word adj lines) and (plurality adj reset adj lines) and (dielectric adj (layer or film)) and (memory adj unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:28
L22	1	substrate and (plurality adj word adj lines) and (plurality adj reset adj lines) and (dielectric adj (layer or film)) and (unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:29
L23	1	substrate and (plurality adj word adj lines) and (plurality adj reset adj lines) and (dielectric adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:29
L24	22	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:29

L25	19	(resistive adj random adj access adj memory) and (bottom adj electrode) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:41
L26	2	(resistance adj random adj access adj memory) and (bottom adj electrode) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:35
L27	2	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film)) and (bottom adj electrode) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:38
L28	22	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film))and (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:39
L29	2	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film)) and (bottom adj electrode) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:39
L30	2	substrate and (word adj line) and (reset adj line) and (dielectric adj (layer or film)) and (bit adj line) and (bottom adj electrode) and (top adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:39
L31	65	(resistive adj random adj access adj memory) and (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:41
L32	12	(resistance adj random adj access adj memory) and (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:43

L33	1	(resistance adj random adj access adj memory) and (reset adj line adj contact adj window)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:44
L34	0	(resistive adj random adj access adj memory) and (reset adj line adj contact adj window)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:44